NSN 5962-01-123-3179

Memory Microcircuit - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5962-01-123-3179
Body Length:
Between 0.355 inches and 0.400 inches
Body Width:
Between 0.355 inches and 0.400 inches
Body Height:
0.090 inches
Maximum Power Dissipation Rating:
175.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and monolithic and bipolar and burn in, mil-std-883, class b and electrostatic sensitive and programmable and
w/buffered output and 3-state output
Inclosure Material:
Glass and metal
Inclosure Configuration:
Flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
12 input
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.5 volts power source
Time Rating Per Chacteristic:
75.00 nanoseconds propagation delay time, low to high level output and 75.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Test Data Document:
82577-932883 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
18 flat leads
Shelf Life:
N/a
Unit Of Measure:

Fiig:

No

Demilitarization: